

60 V, 340 mA dual N-channel Trench MOSFET Rev. 2 — 22 September 2010

Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1.Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	$T_{amb} = 25 \text{ °C};$ $V_{GS} = 10 \text{ V}$	<u>[1]</u> _	-	340	mA
R _{DSon}	drain-source on-state resistance	T _j = 25 °C; V _{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 340 mA dual N-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		
2	G1	gate 1		
3	D2	drain 2		
4	S2	source 2		
5	G2	gate 2		2 5
6	D1	drain 1	1 2 3	

017aaa055

3

3. Ordering information

Table 3. Orc	le 3. Ordering information				
Type number	Package				
	Name	Description	Version		
2N7002BKV	-	plastic surface-mounted package; 6 leads	SOT666		

4. Marking

Table 4.	Marking codes	
Type numb	per	Marking code
2N7002BK	V	ZG

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

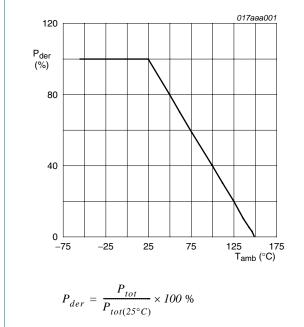
		0, (,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
V _{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	V _{GS} = 10 V	<u>[1]</u>		
		T _{amb} = 25 °C	-	340	mA
		T _{amb} = 100 °C	-	240	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$	-	1.2	A

60 V, 340 mA dual N-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	350	mW
			<u>[1]</u> -	410	mW
		T _{sp} = 25 °C	-	1140	mW
Source-di	rain diode				
I _S	source current	T _{amb} = 25 °C	<u>[1]</u> -	340	mA
ESD max	imum rating				
V _{ESD}	electrostatic discharge voltage	human body model	<u>[3]</u> _	2000	V
Per devic	e				
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	525	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

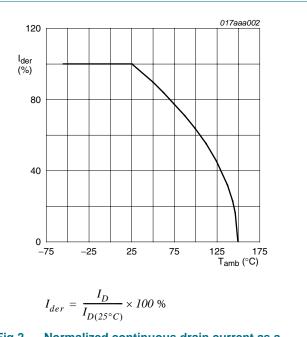
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard [2] footprint.



[3] Measured between all pins.

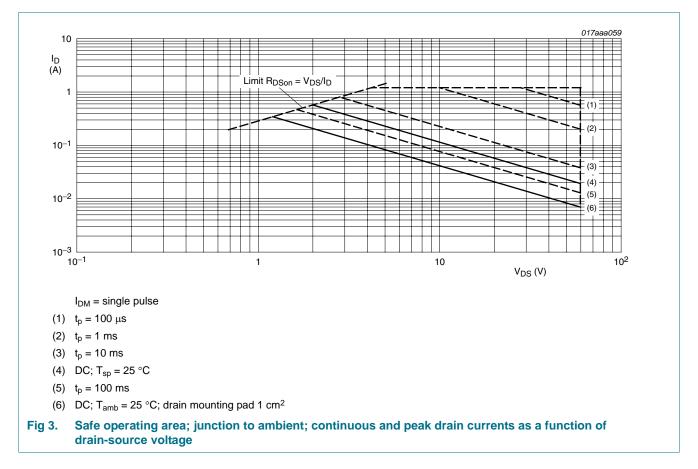
Fig 1. Normalized total power dissipation as a function of ambient temperature





2N7002BKV

60 V, 340 mA dual N-channel Trench MOSFET



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> _	315	360	K/W
	junction to ambient		[2] _	265	305	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	110	K/W
Per device)					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	240	K/W

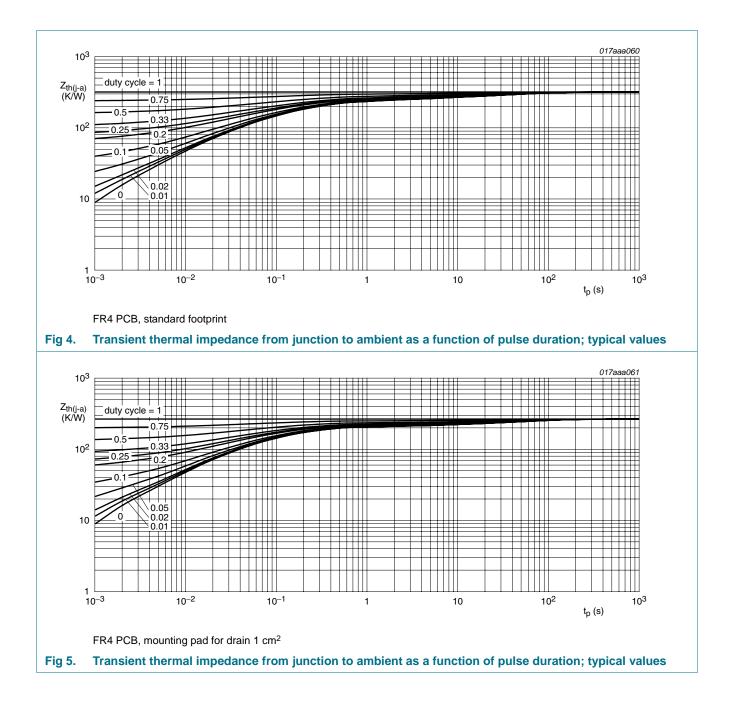
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

Product data sheet

2N7002BKV

60 V, 340 mA dual N-channel Trench MOSFET



60 V, 340 mA dual N-channel Trench MOSFET

7. Characteristics

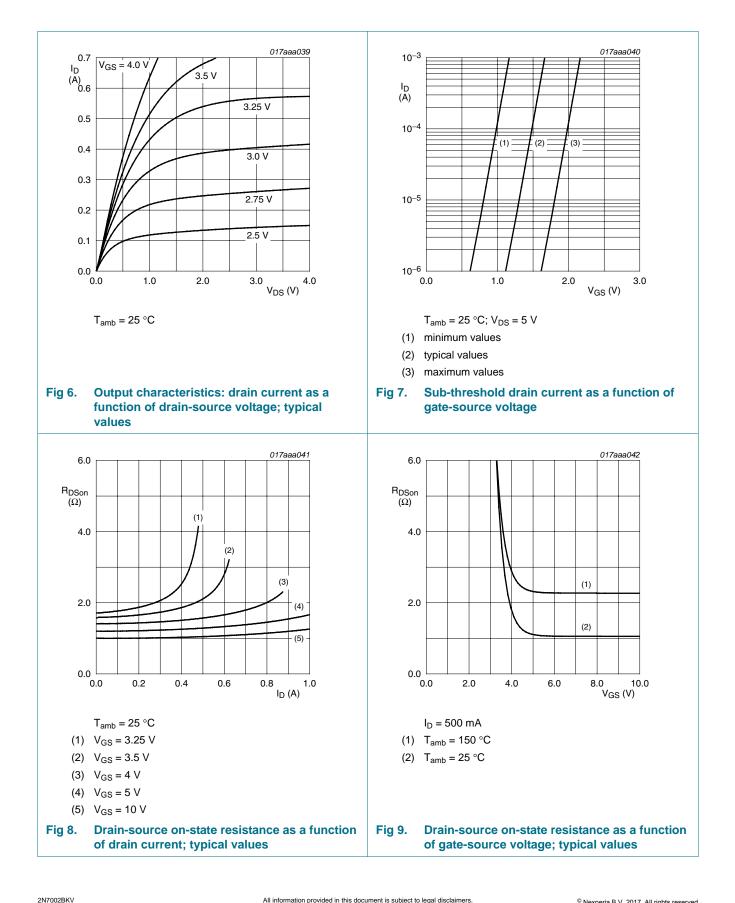
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \ \mu\text{A}; \ V_{GS} = 0 \ V$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μA
		T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V_{GS} = ± 20 V; V_{DS} = 0 V	-	-	10	μA
R _{DSon}	drain-source on-state		<u>[1]</u>			
resistance	resistance	V_{GS} = 5 V; I_D = 50 mA	-	1.3	2	Ω
		V_{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω
g fs	forward transconductance	V_{DS} = 10 V; I _D = 200 mA	<u>[1]</u>	550	-	mS
Dynamic of	characteristics					
Q _{G(tot)}	total gate charge	I _D = 300 mA;	-	0.5	0.6	nC
Q _{GS}	gate-source charge	V _{DS} = 30 V; V _{GS} = 4.5 V	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 10 V;$	-	33	50	pF
C _{oss}	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	рF
t _{d(on)}	turn-on delay time	V _{DD} = 50 V;	-	5	10	ns
t _r	rise time	$R_{L} = 250 \Omega;$	-	6	-	ns
t _{d(off)}	turn-off delay time	– V _{GS} = 10 V; R _G = 6 Ω	-	12	24	ns
t _f	fall time		-	7	-	ns
Source-dr	ain diode					
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V	0.47	0.75	1.1	V

 $\label{eq:point} \begin{tabular}{ll} \end{tabular} \end{tabular} \begin{tabular}{ll} \end{tabular} 1 \end{tabular} \end{tabular} \end{tabular} \end{tabular} \begin{tabular}{ll} \end{tabular} \end{tabular} \end{tabular} \end{tabular} \begin{tabular}{ll} \end{tabular} \end{tabular}$

Product data sheet

2N7002BKV

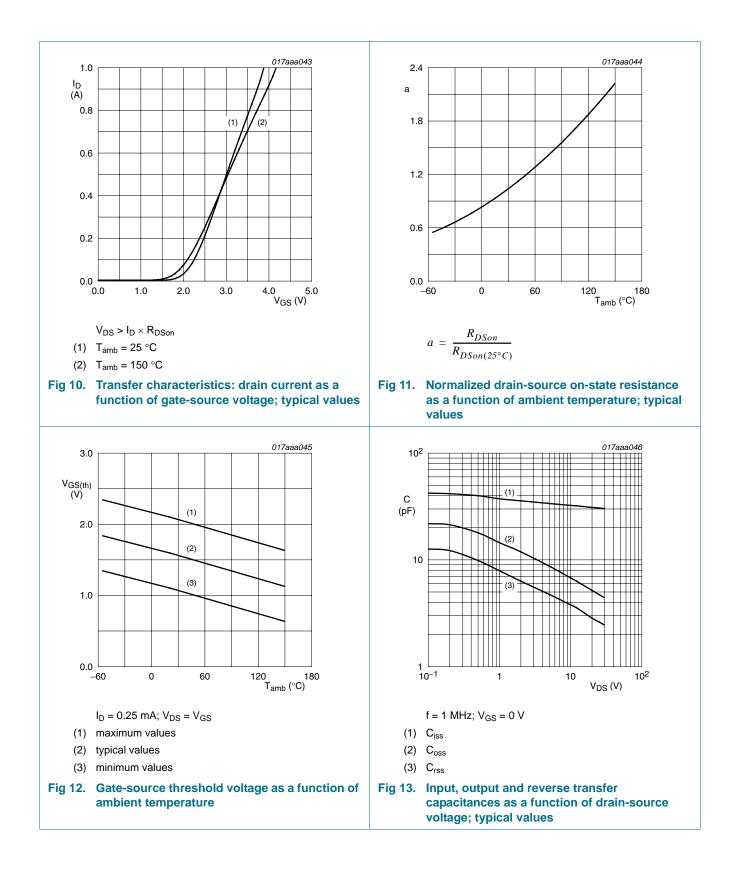
60 V, 340 mA dual N-channel Trench MOSFET



Product data sheet

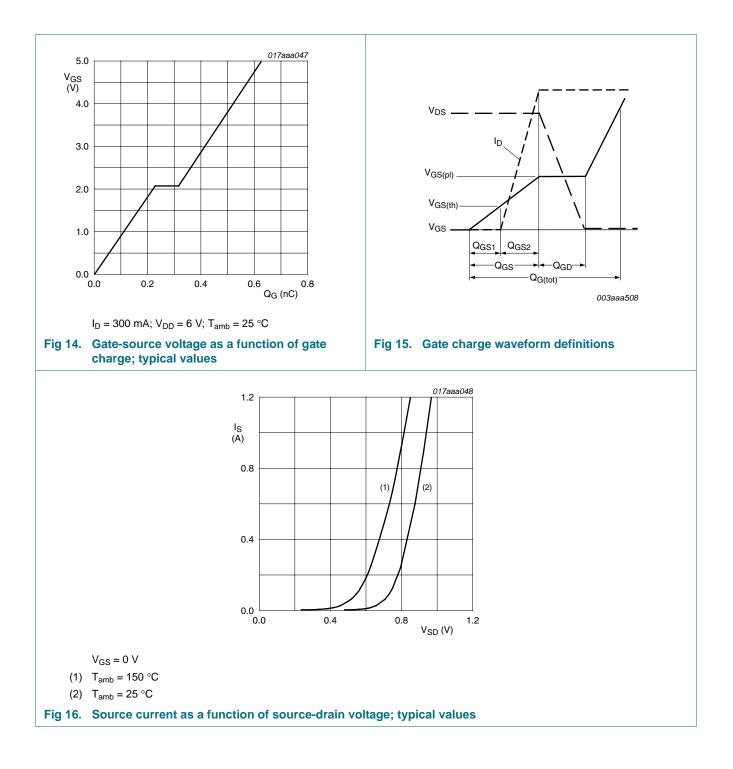
2N7002BKV

60 V, 340 mA dual N-channel Trench MOSFET



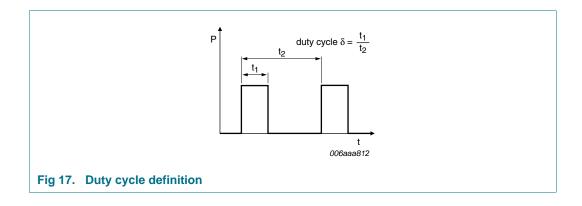
2N7002BKV

60 V, 340 mA dual N-channel Trench MOSFET



60 V, 340 mA dual N-channel Trench MOSFET

8. Test information



60 V, 340 mA dual N-channel Trench MOSFET

9. Package outline

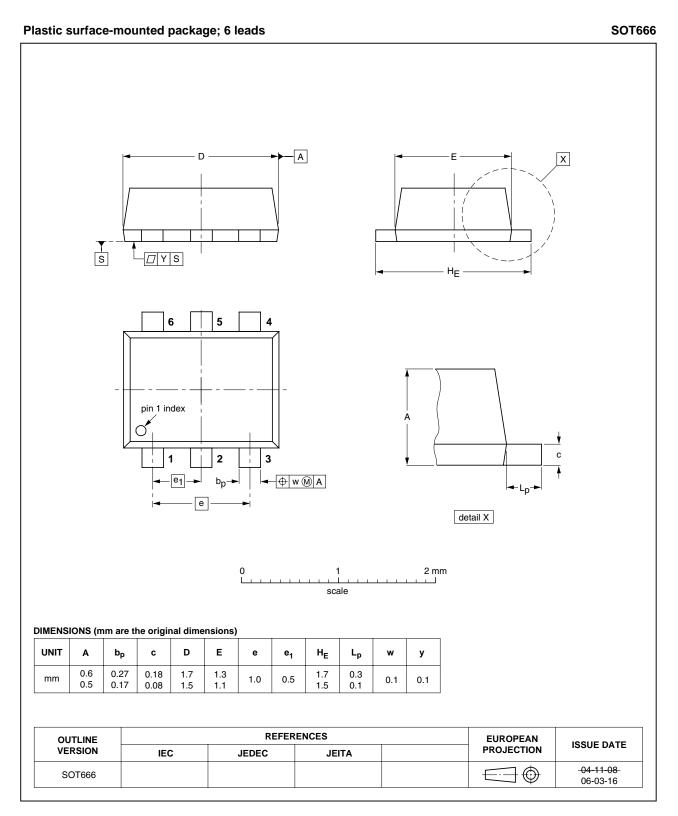
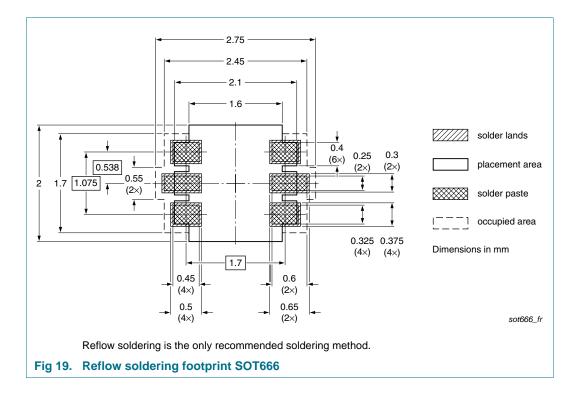


Fig 18. Package outline SOT666

All information provided in this document is subject to legal disclaimers.

60 V, 340 mA dual N-channel Trench MOSFET

10. Soldering



60 V, 340 mA dual N-channel Trench MOSFET

11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Bocument IB	itelease date	Data Sheet Status	Change Hotice	ouperseues
2N7002BKV v.2	20100922	Product data sheet	-	2N7002BKV v.1
Modifications:	 Table 2 "Pin 	ning": graphic symbol ame	nded	
	Table 6 "The	ermal characteristics": typo	for R _{th(j-sp)} maximum va	lue per transistor amended
	• Table 6 "The	ermal characteristics": typo	for R _{th(j-a)} maximum val	ue per device amended
2N7002BKV v.1	20100610	Product data sheet	_	-

60 V, 340 mA dual N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any

representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale - Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

60 V, 340 mA dual N-channel Trench MOSFET

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

60 V, 340 mA dual N-channel Trench MOSFET

14. Contents

1	Product profile 1	
1.1	General description 1	l
1.2	Features and benefits 1	
1.3	Applications 1	
1.4	Quick reference data 1	
2	Pinning information 2	2
3	Ordering information 2	2
4	Marking 2	2
5	Limiting values	2
6	Thermal characteristics 4	ŀ
7	Characteristics	5
8	Test information 10)
9	Package outline 11	l
10	Soldering 12	2
11	Revision history 13	3
12	Legal information 14	ŀ
12.1	Data sheet status 14	ł
12.2	Definitions 14	ł
12.3	Disclaimers 14	ł
12.4	Trademarks 15	5
13	Contact information 15	5
14	Contents 16	;

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by NXP manufacturer:

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3